

SOT-523 Plastic-Encapsulate MOSFET

20V N-Channel MOSFET

Product Summary

| $V_{(BR)DSS}$ | $R_{DS(on)}TYP$ | I_D |
|---------------|-----------------|-------|
| 20V | 170mΩ@-4.5V | 0.75A |
| | 230mΩ@-2.5V | |
| | 330mΩ@-1.8V | |

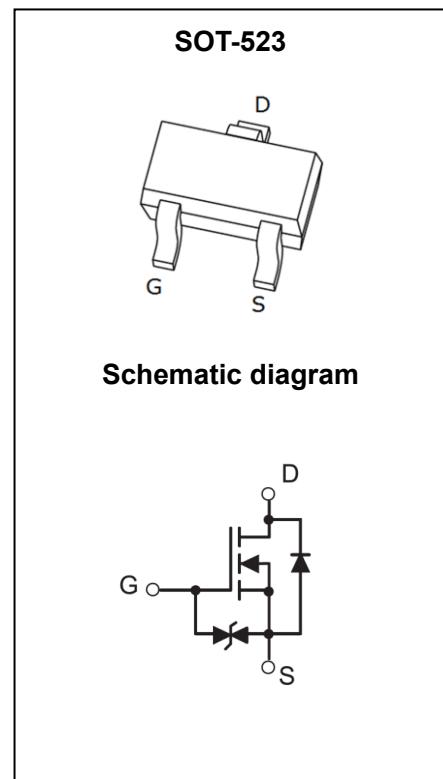
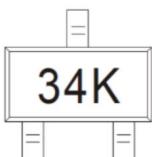
Feature

- Trench Technology Power MOSFET
- Low $R_{DS(ON)}$
- Low Gate Charge
- ESD Protected

Application

- Load Switch
- DC/DC Converter

MARKING:



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

| Parameter | Symbol | Value | Unit |
|--|-----------------|----------|------|
| Drain - Source Voltage | V_{DS} | 20 | V |
| Gate - Source Voltage | V_{GS} | ± 12 | V |
| Continuous Drain Current ^{1,5} | I_D | 0.75 | A |
| Pulsed Drain Current ² | I_{DM} | 3.0 | A |
| Power Dissipation ^{4,5} | P_D | 150 | mW |
| Thermal Resistance from Junction to Ambient ⁵ | $R_{\theta JA}$ | 833 | °C/W |
| Junction Temperature | T_J | 150 | °C |
| Storage Temperature | T_{STG} | -55~+150 | °C |

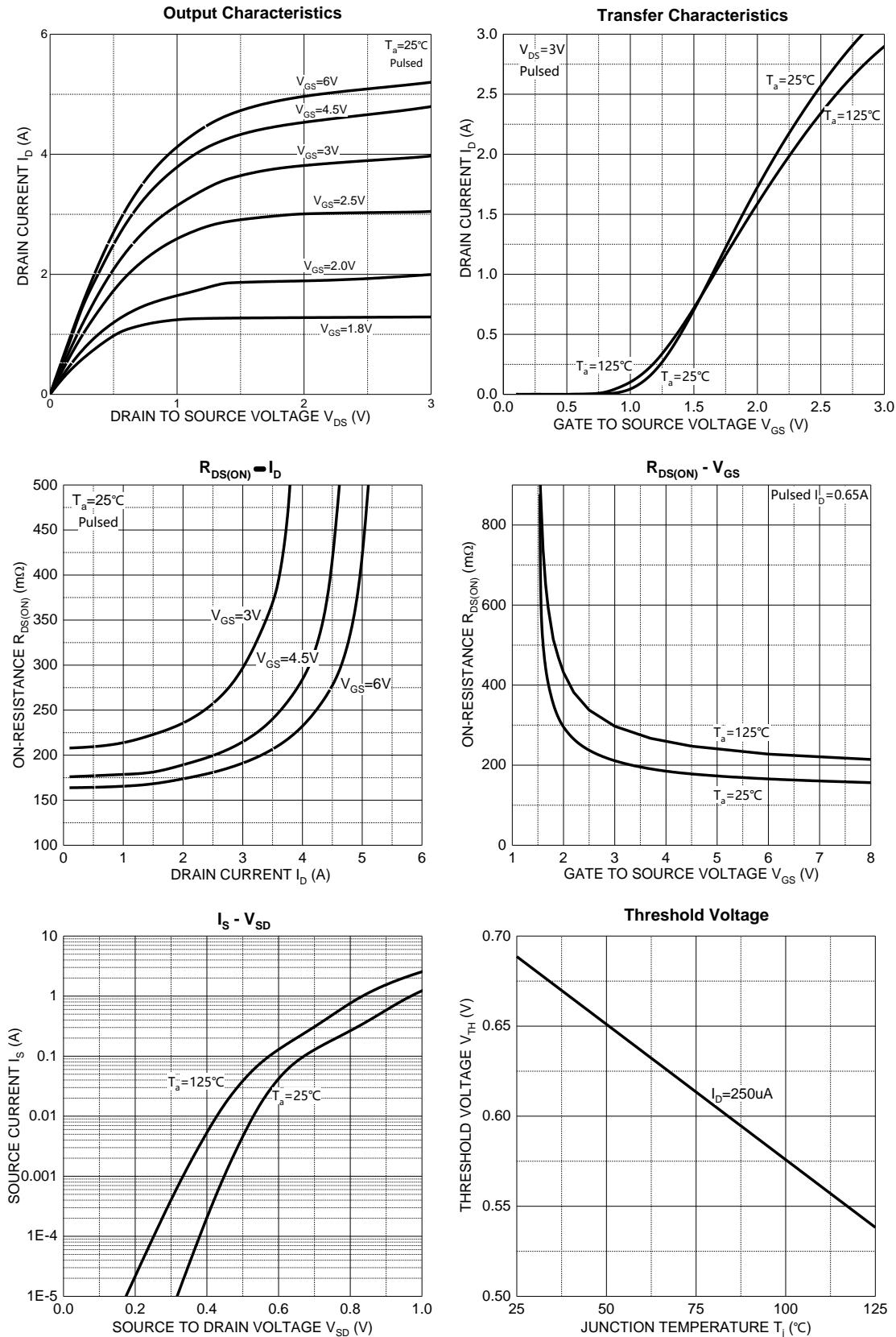
Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

| Parameter | Symbol | Test Condition | Min | Type | Max | Unit |
|---|-----------------------------|--|-----|------|----------|------------------|
| Off Characteristics | | | | | | |
| Drain - Source Breakdown Voltage | $V_{(\text{BR})\text{DSS}}$ | $V_{GS} = 0V, I_D = 250\mu\text{A}$ | 20 | | | V |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS} = 20V, V_{GS} = 0V$ | | | 1 | μA |
| Gate - Body Leakage Current | I_{GSS} | $V_{GS} = \pm 10V, V_{DS} = 0V$ | | | ± 10 | μA |
| On Characteristics³ | | | | | | |
| Gate Threshold Voltage | $V_{GS(\text{th})}$ | $V_{DS} = V_{GS}, I_D = 250\mu\text{A}$ | 0.4 | 0.7 | 1 | V |
| Drain-source On-resistance | $R_{DS(\text{on})}$ | $V_{GS} = -4.5V, I_D = 0.65A$ | | 170 | 380 | $\text{m}\Omega$ |
| | | $V_{GS} = 2.5V, I_D = 0.55A$ | | 230 | 450 | |
| | | $V_{GS} = 1.8V, I_D = 0.45A$ | | 330 | 590 | |
| Dynamic Characteristics | | | | | | |
| Input Capacitance | C_{iss} | $V_{DS} = 10V, f = 1\text{MHz}$ | | 55.6 | | pF |
| Output Capacitance | C_{oss} | | | 15.2 | | |
| Reverse Transfer Capacitance | C_{rss} | | | 10.3 | | |
| Switching Characteristics | | | | | | |
| Total Gate Charge | Q_g | $V_{DD} = 10V, V_{GS} = 4.5V, I_D = 0.65A$ | | 0.78 | | nC |
| Gate-source Charge | Q_{gs} | | | 0.23 | | |
| Gate-drain Charge | Q_{gd} | | | 0.01 | | |
| Turn-on Delay Time | $t_{d(\text{on})}$ | $V_{DS} = 10V, V_{GS} = 4.5V$ $I_D = 0.5A, R_{\text{GEN}} = 10\Omega$ | | 6.7 | | ns |
| Turn-on Rise Time | t_r | | | 4.8 | | |
| Turn-off Delay Time | $t_{d(\text{off})}$ | | | 17.3 | | |
| Turn-off Fall Time | t_f | | | 7.4 | | |
| Source - Drain Diode Characteristics | | | | | | |
| Diode Forward Voltage ³ | V_{SD} | $V_{GS} = 0V, I_s = 0.15A$ | | | 1.2 | V |

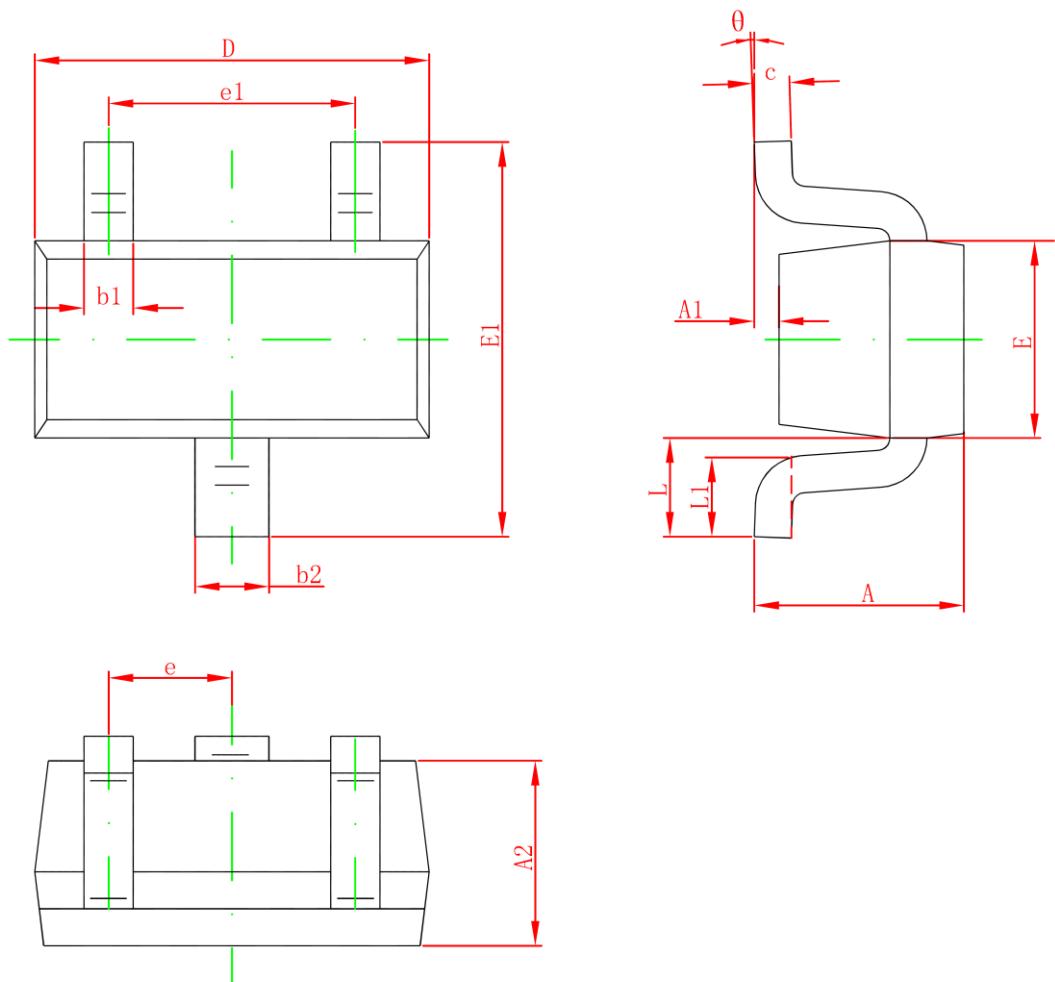
Notes :

1. The maximum current rating is limited by package.
2. Pulse Test : Pulse Width $\leq 10\mu\text{s}$, duty cycle $\leq 1\%$.
3. Pulse Test : Pulse Width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.
4. The power dissipation P_D is limited by $T_{J(\text{MAX})} = 150^\circ\text{C}$.
5. Device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$.

Typical Characteristics



SOT-523 Package Outline Dimensions



| Symbol | Dimensions In Millimeters | | Dimensions In Inches | |
|--------|---------------------------|-------|----------------------|-------|
| | Min. | Max. | Min. | Max. |
| A | 0.700 | 0.900 | 0.028 | 0.035 |
| A1 | 0.000 | 0.100 | 0.000 | 0.004 |
| A2 | 0.700 | 0.800 | 0.028 | 0.031 |
| b1 | 0.150 | 0.250 | 0.006 | 0.010 |
| b2 | 0.250 | 0.350 | 0.010 | 0.014 |
| c | 0.100 | 0.200 | 0.004 | 0.008 |
| D | 1.500 | 1.700 | 0.059 | 0.067 |
| E | 0.700 | 0.900 | 0.028 | 0.035 |
| E1 | 1.450 | 1.750 | 0.057 | 0.069 |
| e | 0.900 | 1.100 | 0.035 | 0.043 |
| e1 | 0.500TYP | | 0.020TYP | |
| L | 0.400REF | | 0.016REF | |
| L1 | 0.260 | 0.460 | 0.010 | 0.018 |
| theta | 0° | 8° | 0° | 8° |